

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	14	("4396458" "4440804" "4601097" "4830986" "5162933" "5317433" "5339181" "5462887" "5668379" "5731856" "5771083" "5793460" "5847781" "7078279").PN. OR ("7220612").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/08/03 10:58
L7	145	(438/38).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/08/03 10:59
L8	185	(438/951).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/08/03 11:11
L9	3	438/30.ccls. and ((lift adj1 off) near10 ((passivation protection) near2 (layer film)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/03 11:14
L10	4	438/30.ccls. and ((lift adj1 off) with ((passivation protection) near2 (layer film)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/03 11:15
L11	20	((lift adj1 off) with ((passivation protection) near2 (layer film))).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/03 11:20
L12	8	("20020140889" "20040063254" "20050077516" "20050077522" "4684435" "5391507" "5953595" "6376288").PN. OR ("7005332").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/08/03 11:19
L13	8	((organic photoresist resist) near2 (film layer)) with ((passivation protection) near2 (layer film)) with (pixel near2 electrode) with pad).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/03 11:22
L14	72	((organic photoresist resist) near2 (film layer)) with ((passivation protection) near2 (layer film)) with (pixel near2 electrode)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/03 11:22

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S45	211	((pattern\$3 etch\$3) near6 (pixel and drain and source and (semiconductor active))) with (simultaneous\$2 single one concurrent\$2 "same")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 18:03
S46	300	((pattern\$3 etch\$3) near6 (pixel and drain and source and (semiconductor active))) with (simultaneous\$2 single one concurrent\$2 "same")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 18:03